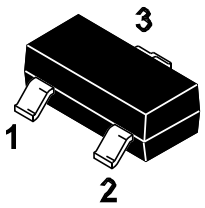
PJM3406NSA
N-Channel Enhancement Mode Power MOSFET

Features

- Advanced Trench Technology
- Excellent $R_{DS(on)}$ and Low Gate Charge
- V_{DS}= 30V,I_D= 4A
  $R_{DS(on)}$< 38mΩ @V_{GS}= 10V

SOT-23



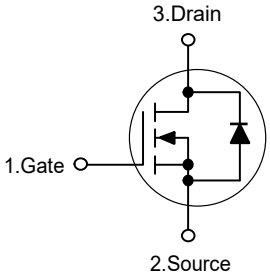
1. Gate 2.Source 3.Drain

Marking Code:R6

Applications

- PWM applications
- Load switch
- Power management

Schematic Diagram



Absolute Maximum Ratings

Ratings at 25℃ ambient temperature unless otherwise specified.

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	4	A
Drain Current-Pulsed Note1	I_{DM}	16	A
Maximum Power Dissipation	P_D	1	W
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C

Thermal Characteristics

Thermal Resistance,Junction-to-Ambient Note2	$R_{\theta JA}$	125	°C/W

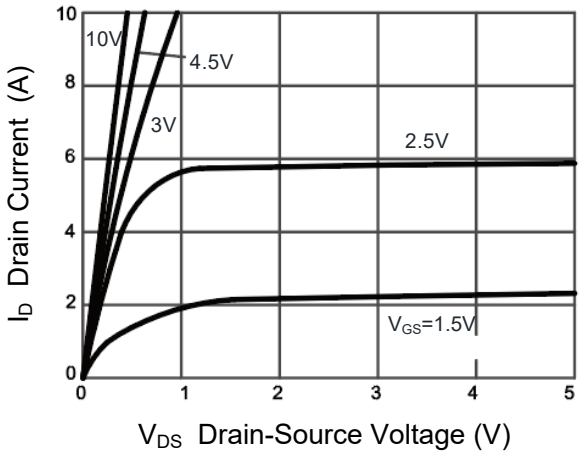
Electrical Characteristics

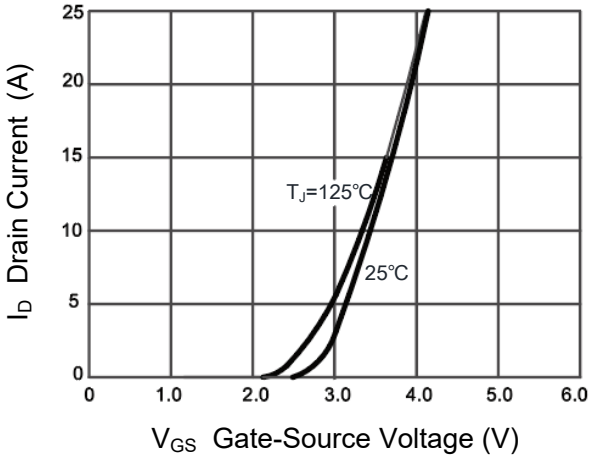
(Ta=25℃ unless otherwise specified)

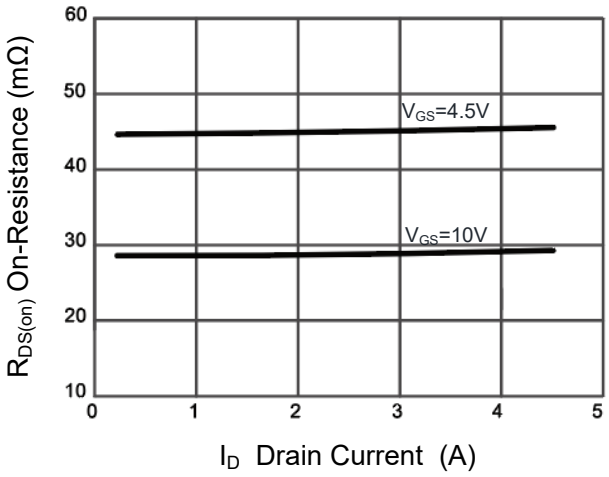
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=250μA	30	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V,V_{GS}=0V	--	--	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	--	--	±100	nA
Gate Threshold Voltage Note3	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	1.0	1.5	2.5	V
Drain-Source On-Resistance Note3	$R_{DS(on)}$	V_{GS}=10V,I_D=4A	--	29	38	mΩ
		V_{GS}=4.5V,I_D=3A	--	45	65	mΩ
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=15V,V_{GS}=0V,f=1MHz	--	233	--	pF
Output Capacitance	C_{oss}		--	44	--	pF
Reverse Transfer Capacitance	C_{rss}		--	33	--	pF
Switching Characteristics						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=15V, I_D=4A, V_{GS}=10V,R_{GEN}=3Ω	--	4	--	nS
Turn-on Rise Time	t_r		--	2.1	--	nS
Turn-off Delay Time	$t_{d(off)}$		--	15	--	nS
Turn-off Fall Time	t_f		--	3.2	--	nS
Total Gate Charge	Q_g	V_{DS}=15V,I_D=2A, V_{GS}=10V	--	3	--	nC
Gate-Source Charge	Q_{gs}		--	0.5	--	nC
Gate-Drain Charge	Q_{gd}		--	0.8	--	nC
Source-Drain Diode Characteristics						
Diode Forward Voltage Note3	V_{SD}	V_{GS}=0V,I_S=4A	--	--	1.2	V
Diode Forward Current Note2	I_S		--	--	4	A

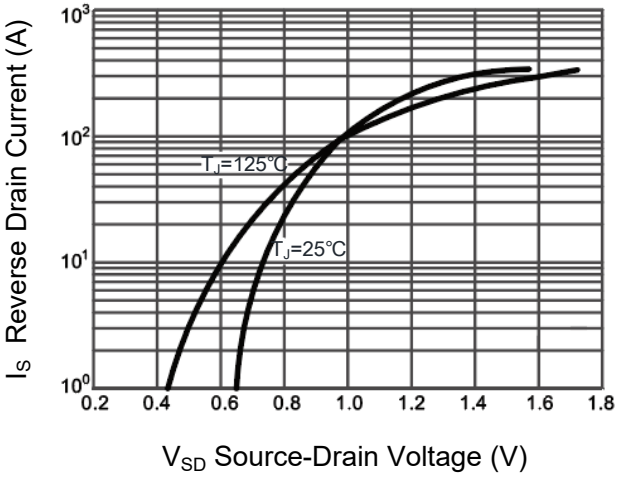
Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse width≤300μs, duty cycle≤2%.

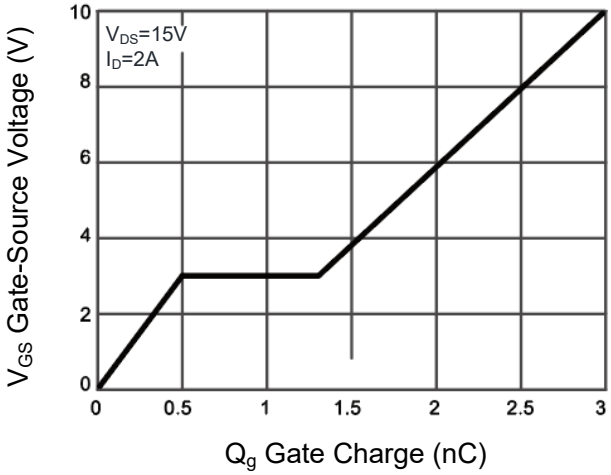
Typical Characteristic Curves

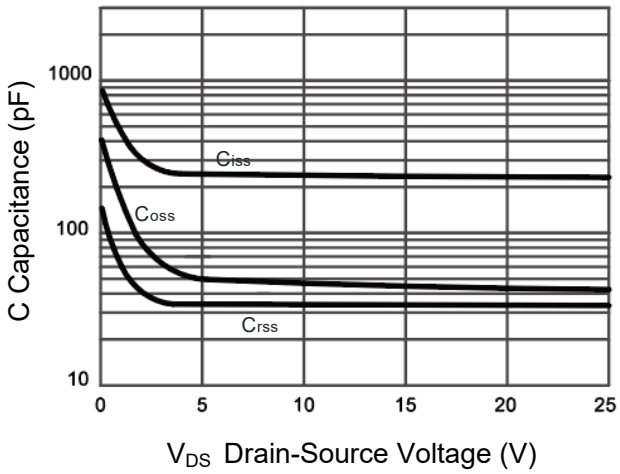


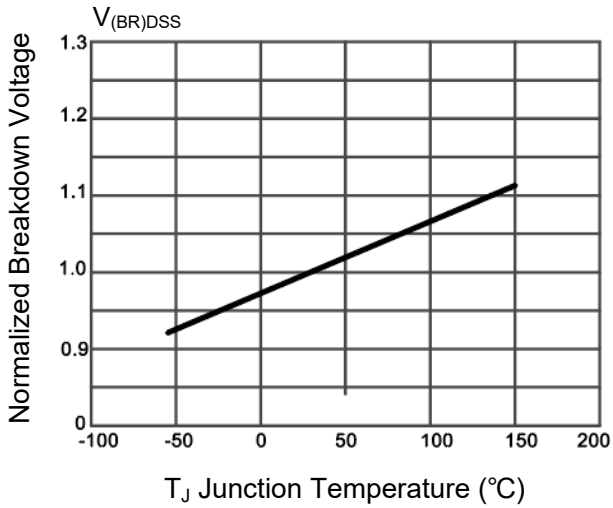


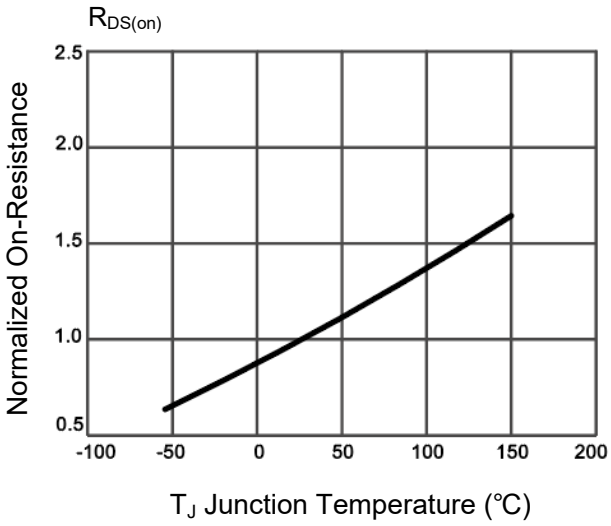


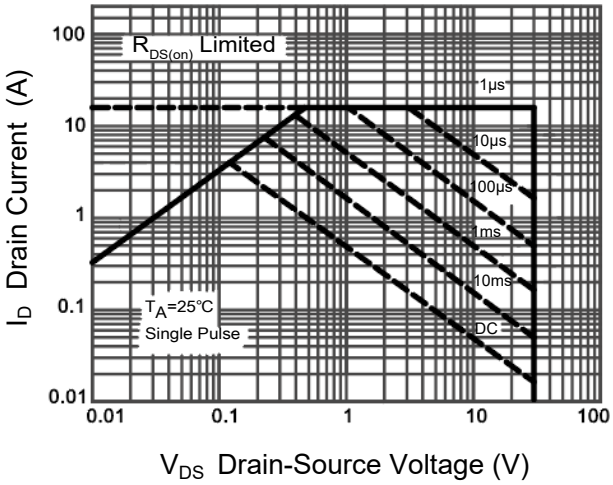







V(BR)DSS
Normalized Breakdown Voltage
1.3
1.2
1.1
1.0
0.9
0
-100
-50
0
50
100
150
200
TJ Junction Temperature (℃)

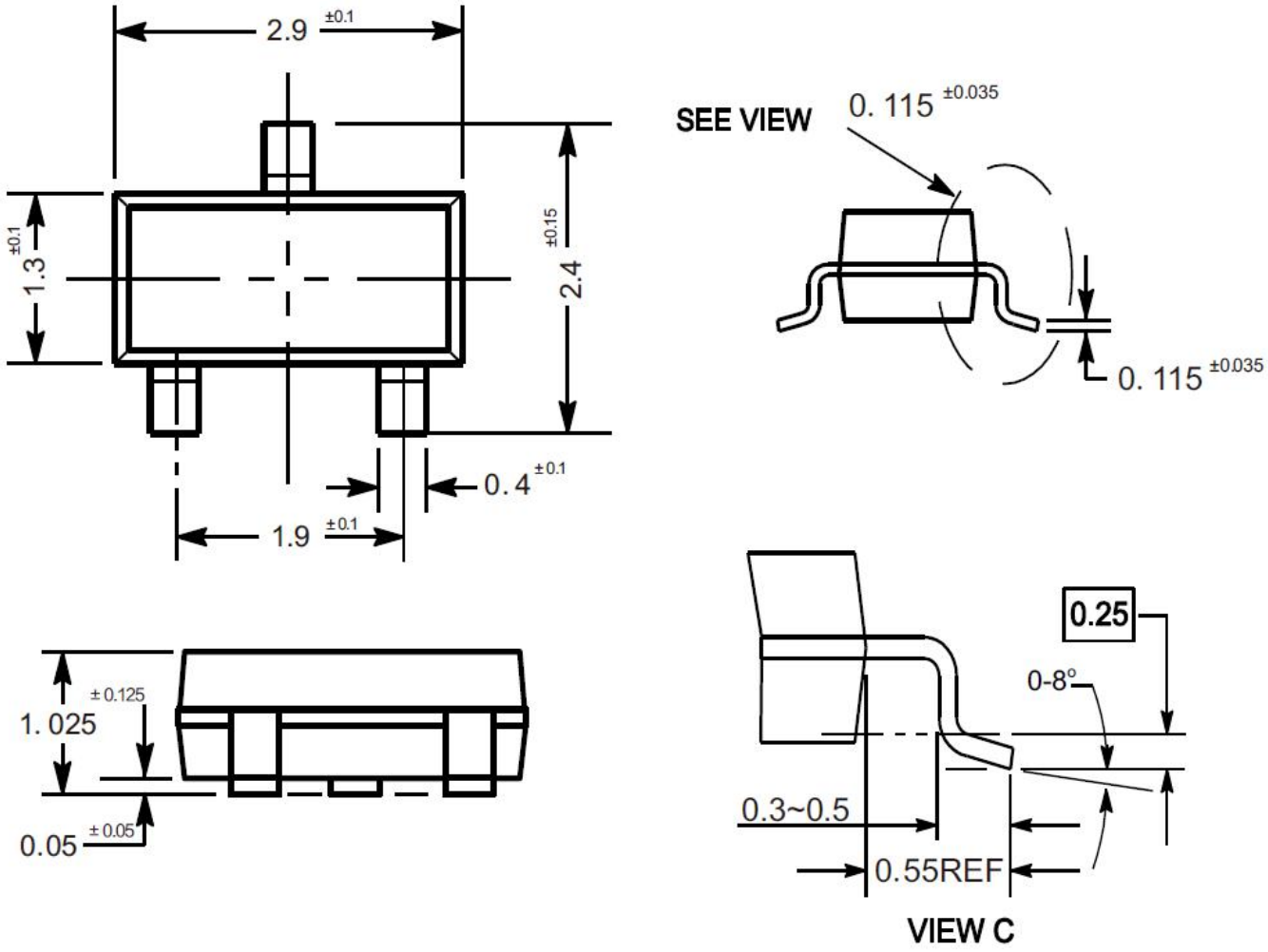

RDS(on)
Normalized On-Resistance
2.5
2.0
1.5
1.0
0.5
-100
-50
0
50
100
150
200
TJ Junction Temperature (℃)


RDS(on) Limited
1μs
10μs
100μs
1ms
10ms
DC
TA=25℃
Single Pulse
ID Drain Current (A)
100
10
1
0.1
0.01
0.01
0.1
1
10
100
VDS Drain-Source Voltage (V)

Package Outline

SOT-23

Dimensions in mm

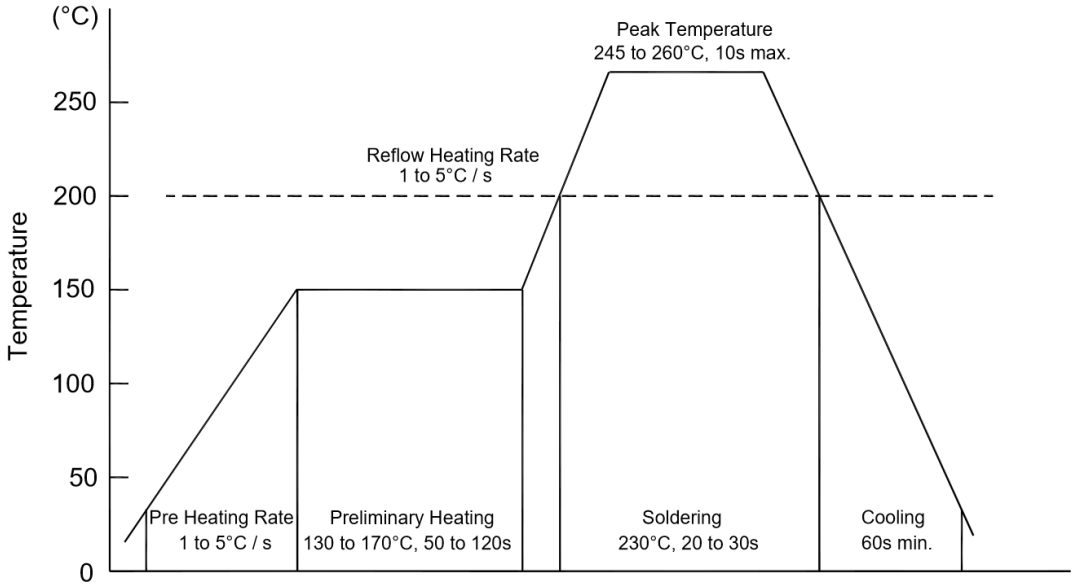


Ordering Information

Device	Package	Shipping
PJM3406NSA	SOT-23	3,000PCS/Reel&7inches

Conditions of Soldering and Storage

◆ Recommended condition of reflow soldering



Recommended peak temperature is over 245 ^{O}C. If peak temperature is below 245 ^{O}C, you may adjust the following parameters:

- Time length of peak temperature (longer)
- Time length of soldering (longer)
- Thickness of solder paste (thicker)

◆ Conditions of hand soldering

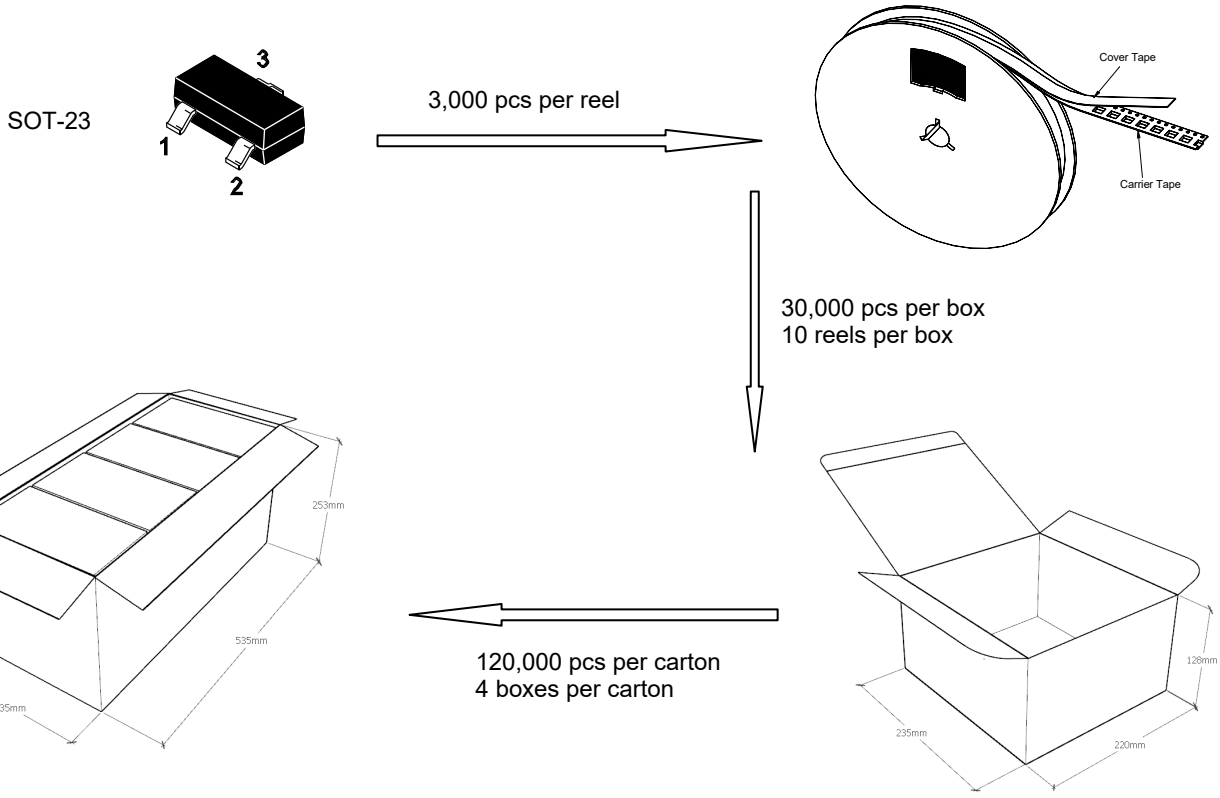
- Temperature: 370 ^{O}C
- Time: 3s max.
- Times: one time

◆ Storage conditions

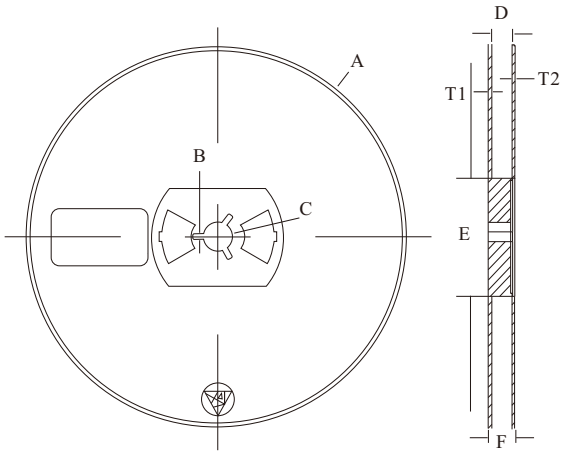
- **Temperature**
  5 to 40 ^{O}C
- **Humidity**
  30 to 80% RH
- **Recommended period**
  One year after manufacturing

Package Specifications

- The method of packaging



◆ Embossed tape and reel data



Symbol	Value (unit: mm)
A	Ø 177.8±1
B	2.7±0.2
C	Ø 13.5±0.2
E	Ø 54.5±0.2
F	12.3±0.3
D	9.6+2/-0.3
T1	1.0±0.2
T2	1.2±0.2

Reel (7")